



IXTF230N085T Information



For Reference Only

Part Number IXTF230N085T

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 85V 130A ISOPLUS I4

Package i4-Pac?-5

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTF230N085T Specifications

| Manufacturer Part Number IXTF230N085T Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package i4-Pac?-5 Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 85V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs 187nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | | |
|--|--|--------------------------------------|
| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single id-Pac?-5 Series FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Dysard (Max | Manufacturer Part Number | IXTF230N085T |
| Package i4-Pac?-5 Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 85V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs 187nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Manufacturer | IXYS |
| Package i4-Pac?-5 Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 85V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs 187nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Category | Discrete Semiconductor Products |
| Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 85V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs 187nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | | Transistors - FETs, MOSFETs - Single |
| FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 85V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs 187nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature 55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case is 4-Pac?-5 | Package | i4-Pac?-5 |
| Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package Package / Case MOSFET (Metal Oxide) 85V MOSFET (Metal Oxide) 85V 85V 85V 85V 85V 180A (Tc) 180V 9900PF 25V 25V 25V 20V 75°C (TJ) Through Hole Supplier Device Package ISOPLUS i4-PAC? 14-Pac?-5 | Series | TrenchMV? |
| Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 85V 130A (Tc) 140V 250mA 187nC @ 10V 187nC @ | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature Supplier Device Package Package / Case 130A (Tc) 140A 150PLUS i4-PAC? 150PLUS i4-PAC? 140A 150PLUS i4-PAC? | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature Supplier Device Package Package / Case 10V 4V @ 250mA 187nC @ 10V 9900pF @ 25V ±20V 5.3 wOhm @ 50A, 10V 5.3 mOhm @ 50A, 10V Through Hole Supplier Device Package | Drain to Source Voltage (Vdss) | 85V |
| Vgs(th) (Max) @ Id 4V @ 250mA Gate Charge (Qg) (Max) @ Vgs 187nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Current - Continuous Drain (Id) @ 25°C | 130A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V Vgs (Max) E20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Vgs(th) (Max) @ Id | 4V @ 250mA |
| Vgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs5.3 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageISOPLUS i4-PAC?Package / Casei4-Pac?-5 | Gate Charge (Qg) (Max) @ Vgs | 187nC @ 10V |
| FET Feature - Common Co | Input Capacitance (Ciss) (Max) @ Vds | 9900pF @ 25V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs5.3 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageISOPLUS i4-PAC?Package / Casei4-Pac?-5 | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Power Dissipation (Max) | 200W (Tc) |
| Mounting Type Through Hole Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Rds On (Max) @ Id, Vgs | 5.3 mOhm @ 50A, 10V |
| Supplier Device Package ISOPLUS i4-PAC? Package / Case i4-Pac?-5 | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case i4-Pac?-5 | Mounting Type | Through Hole |
| | Supplier Device Package | ISOPLUS i4-PAC? |
| D (0 | Package / Case | i4-Pac?-5 |
| Report errors? | | Report errors? |

IXTF230N085T Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTF230N085T Payment Methods



















IXTF230N085T Shipping Methods













If you have any question about IXTF230N085T, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com